

SOT223 NPN SILICON PLANAR HIGH PERFORMANCE TRANSISTOR

FZT655

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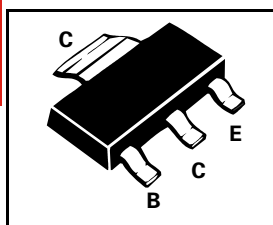
FEATURES

- * Low saturation voltage

勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-54151736
 勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

COMPLEMENTARY TYPE - FZT755

PARTMARKING DETAIL - FZT655



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	150	V
Collector-Emitter Voltage	V_{CEO}	150	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current	I_{CM}	2	A
Continuous Collector Current	I_C	1	A
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	2	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	150			V	$I_C=100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	150			V	$I_C=10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	$I_E=100\mu A$
Collector Cut-Off Current	I_{CBO}			0.1	μA	$V_{CB}=125V$
Emitter Cut-Off Current	I_{EBO}			0.1	μA	$V_{EB}=3V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.5 0.5	V	$I_C=500mA, I_B=50mA^*$ $I_C=1A, I_B=200mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			1.1	V	$I_C=500mA, I_B=50mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			1.0	V	$I_C=500mA, V_{CE}=5V^*$
Static Forward Current Transfer Ratio	h_{FE}	50 50 20		300		$I_C=10mA, V_{CE}=5V^*$ $I_C=500mA, V_{CE}=5V^*$ $I_C=1A, V_{CE}=5V^*$
Transition Frequency	f_T	30			MHz	$I_C=10mA, V_{CE}=20V$ $f=20MHz$
Output Capacitance	C_{obo}			20	pF	$V_{CB}=10V, f=1MHz$

*Measured under pulsed conditions. Pulse Width=300 μs . Duty cycle $\leq 2\%$

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TYPICAL CHARACTERISTICS

